

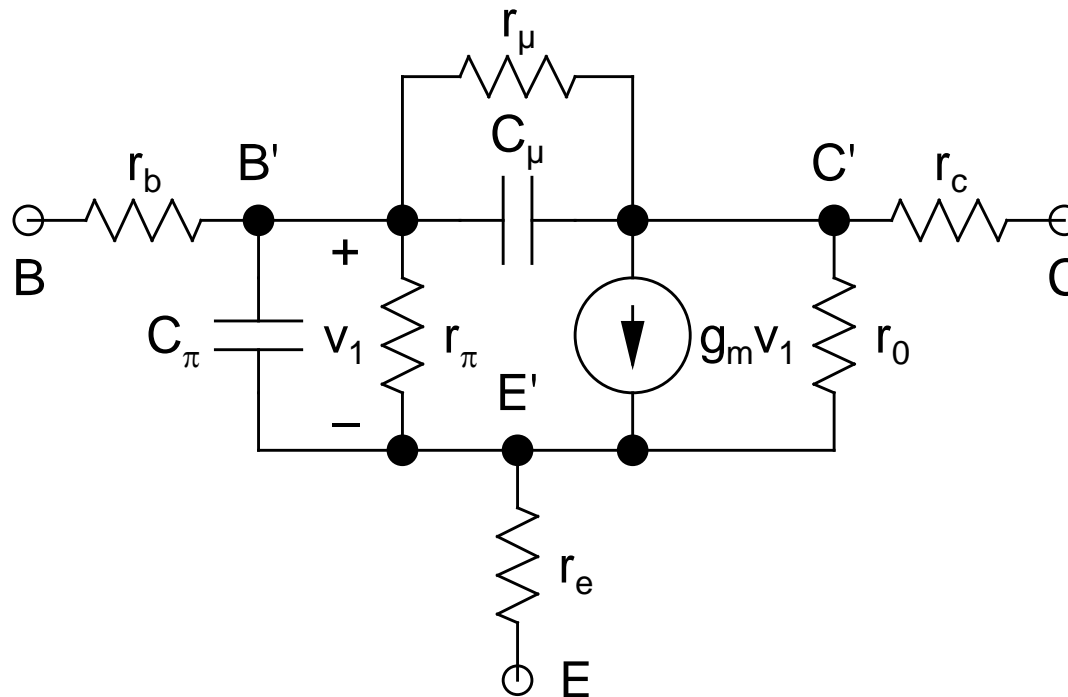
- **Collector-Base Capacitance** (C_μ):

$$C_\mu = \frac{C_{\mu 0}}{\left(1 - \frac{V_{BC}}{V_{0,BC}}\right)^m}$$

- $C_{\mu 0}$: **Collector-base depletion capacitance at zero bias**
- $V_{0,BC}$: **Built-in voltage of collector-base junction**
- m : **Grading coefficient** ($1/2$ for **abrupt step junction**, $1/3$ for **linearly graded junction**)

- *Quasi-Neutral Emitter, Base, and Collector Resistances* (r_e , r_b , and r_c):
 - In *IC BJT*, *emitter highest doped*, *followed by base*, with *collector being least doped*
 - Thus, $r_c > r_b > r_e$
 - *Typical values*:
 - $r_e \sim 5\text{-}10\ \Omega$
 - $r_b \sim 100\text{-}200\ \Omega$
 - $r_c \sim$ can be as high as $\text{k}\Omega$
 - *Become important only at very high frequencies*

The Hybrid- π Model

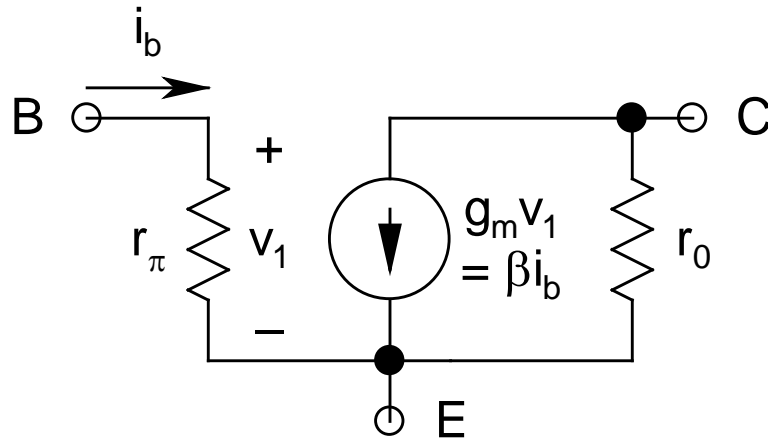


E, B, C: Extrinsic (or External) Terminals

E', B', C': Intrinsic (or Internal) Terminals

- *Simplifications:*

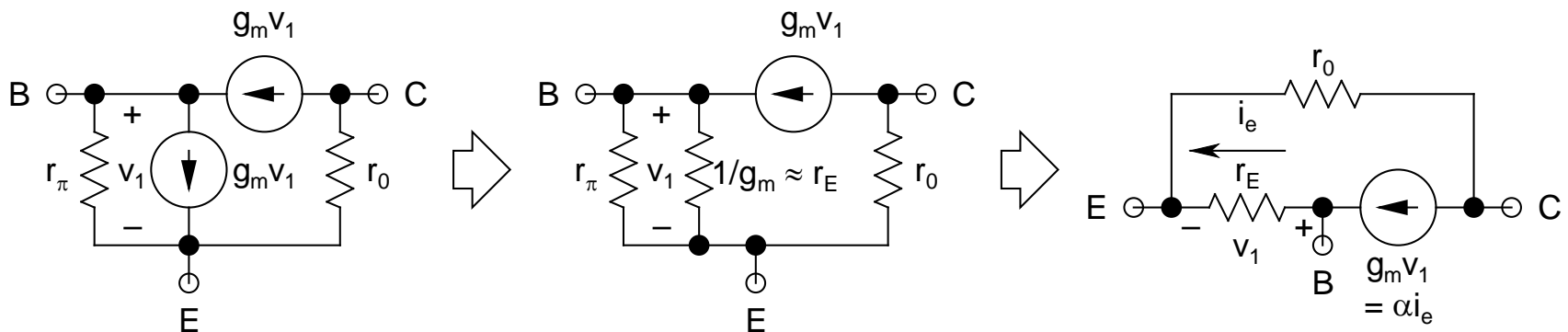
- r_e, r_b, r_c can be *safely neglected* under *low to moderate frequencies* of operation
- r_μ can be *neglected*, since it's *extremely large*
- At *low to moderate frequencies*, the *capacitive reactances* of C_π and C_μ will be *extremely large* \Rightarrow can be *neglected*
- Leads to the *Low-Frequency T-Model*, having only *three components*: r_π , $g_m v_1$, and r_o
- *Simplest possible equivalent results if r_o is also neglected!*



Low-Frequency T-Model

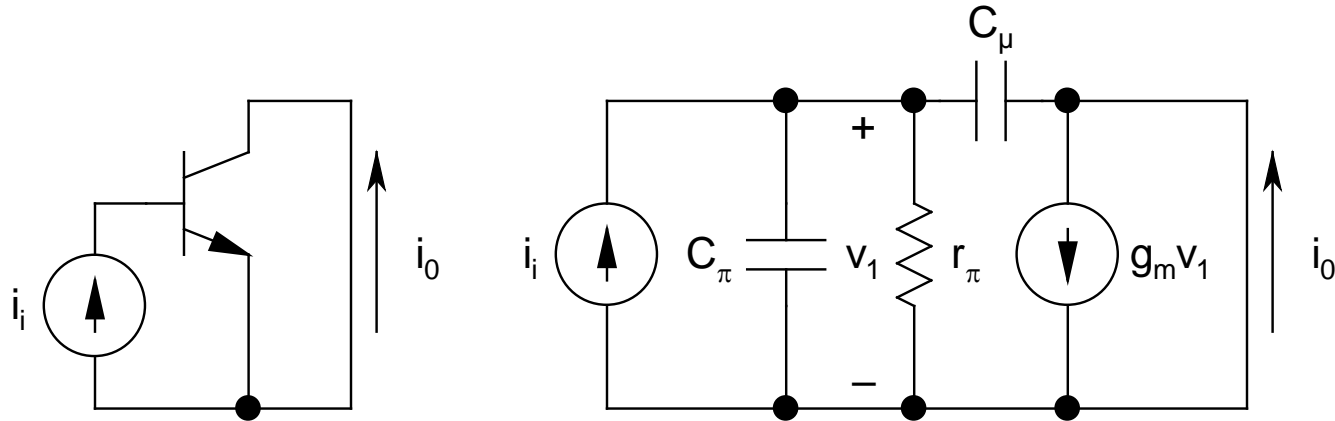
- **Note:** The *output circuit* resembles a **non-ideal current source** of *magnitude* $g_m v_1$ (or equivalently, βi_b) with *output resistance* r_o

- *This model is appropriate when the ac input is applied to base*
- *When the ac input is applied to the emitter, then need to draw this circuit in a slightly different way*



Frequency Specifications of BJTs

- *Four important characteristic frequencies:*
 - *Beta Cutoff Frequency* (f_{β})
 - *Unity Gain Cutoff Frequency* (f_T)
 - *Alpha Cutoff Frequency* (f_{α})
 - *Maximum Operable Frequency* (f_{\max})



- $i_o \approx g_m v_1$ (*neglecting reverse transmission through C_μ*)
- $v_1 = i_i Z_{eq}$

$$Z_{eq} = \frac{r_\pi}{1 + s r_\pi (C_\pi + C_\mu)} \quad (s = j\omega)$$

- Thus:

$$\beta(j\omega) = \frac{i_o(j\omega)}{i_i(j\omega)} = \frac{\beta_0}{1 + j\omega/\omega_\beta}$$

$\beta_0 (= g_m r_\pi)$: *Low-frequency short-circuit common-emitter current gain*

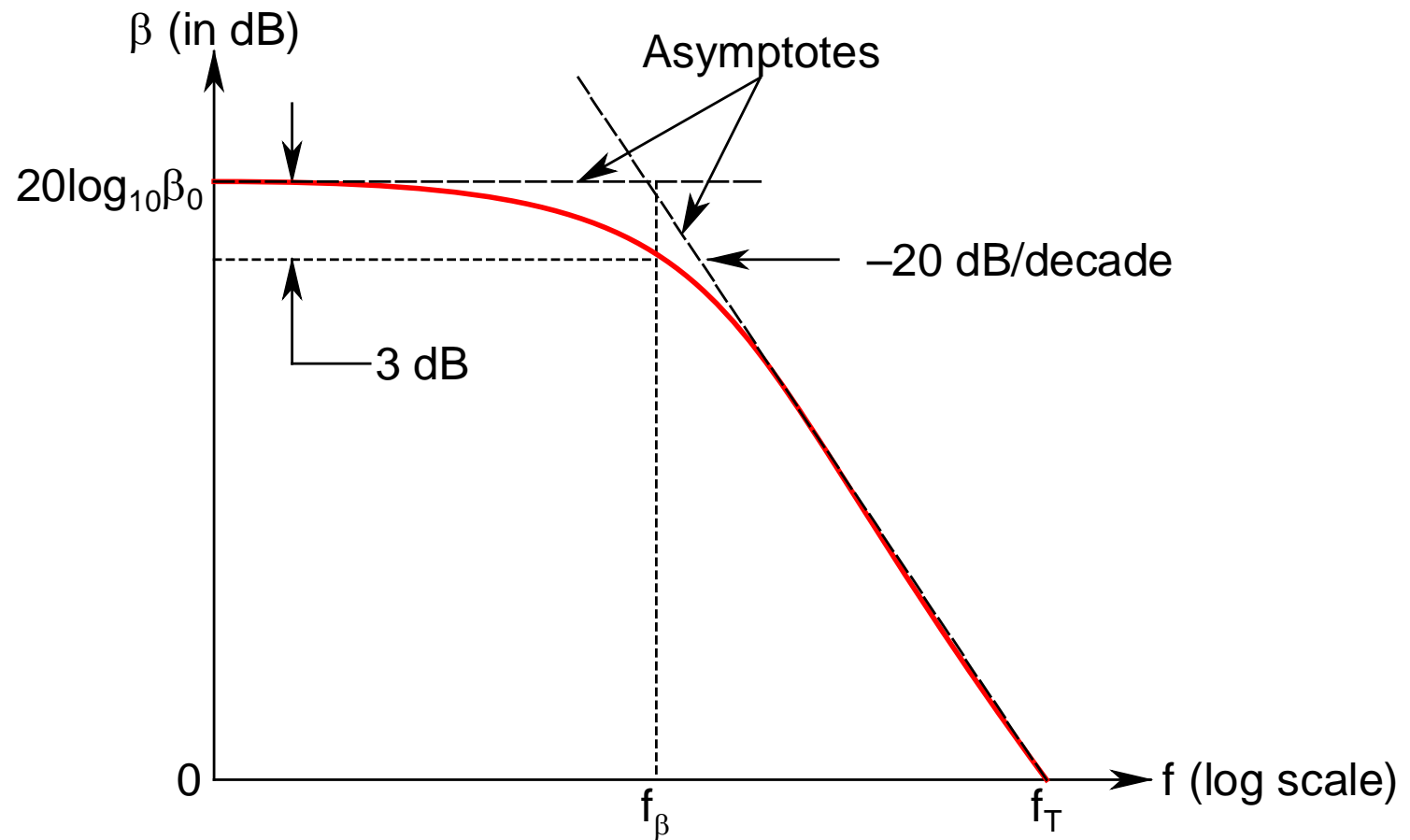
$$\omega_\beta = \frac{g_m}{\beta_0 (C_\pi + C_\mu)}$$

- $f_\beta [= \omega_\beta/(2\pi)]$: *Beta Cutoff Frequency*
- At $f = f_\beta$, $\beta = \beta_0/\sqrt{2}$

- For $f \gg f_\beta$:

$$\beta(j\omega) \simeq \frac{g_m}{j\omega(C_\pi + C_\mu)}$$

- At $\omega = \omega_T = g_m/(C_\pi + C_\mu)$, $|\beta| = 1$
- $f_T [= \omega_T/(2\pi)]$: ***Unity Gain Cutoff Frequency*** (also known as ***Unity Gain Bandwidth***)
- **Note**: $f_T = \beta_0 f_\beta$
- ***$f_T > f_\beta$, and their spacing depends on β_0***



- *Actual measurement of f_T difficult - measured indirectly*
- *Measurement done at $f_x \gg f_\beta$, where β has dropped to about 5-10*
- Then, $f_T = \beta(f_x)f_x$
- Using $\alpha = \beta/(\beta + 1)$:

$$\alpha(j\omega) = \frac{\beta(j\omega)}{1 + \beta(j\omega)} = \frac{\alpha_0}{1 + j\omega/\omega_\alpha}$$

$$\alpha_0 [= \beta_0/(\beta_0 + 1)]: \text{ *Low-frequency short-circuit common-base current gain* }$$